

BIPOLAR TRANSISTOR HAVING SELF-ALIGNED SILICIDE AND A SELF-ALIGNED EMITTER CONTACT BORDER

ABTRACT OF THE DISCLOSURE

The present invention provides a bipolar transistor having a raised extrinsic base silicide and an emitter contact border that are self-aligned. The bipolar transistor of the present invention exhibit reduced parasitics as compared with bipolar transistors that do not include a self-aligned silicide and a self-aligned emitter contact border. The present invention also is related to methods of fabricating the inventive bipolar transistor structure. In the methods of the present invention, a block emitter polysilicon region replaces a conventional T-shaped emitter polysilicon.